Single-walled carbon nanotube weak links in Kondo regime with zero-field splitting

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We have investigated proximity-induced supercurrents in single-walled carbon nanotubes in the Kondo regime and compared them with supercurrents obtained on the same tube with Fabry-Pérot resonances. Our data display a wide distribution of Kondo temperatures $T_K=1–14$ K, and the measured critical current $I_{CM}$ vs $T_K$ displays two distinct branches; these branches, distinguished by zero-field splitting of the normal-state Kondo conductance peak, differ by an order of magnitude at large values of $T_K$. Evidence for renormalization of Andreev levels in Kondo regime is also found.

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An odd unpaired electron in a strongly coupled quantum dot makes the dot to behave as a magnetic impurity screened by delocalized electrons. Such a Kondo impurity creates a peak in the density of states at the Fermi level, thereby leading to characteristic Kondo resonances with enhanced conductance around zero bias, which has been observed in various quantum dot systems during the recent years. By studying low-bias transport and multiple Andreev reflections (MAR) in multiwalled carbon nanotubes (MWNTs) contacted by superconducting leads, it has been demonstrated that the Kondo resonances survive the superconductivity of the leads when the Kondo temperature $T_K$ exceeds the superconducting gap $\Delta$ (Ref. 4); thus, intricate interplay between Kondo behavior and superconductivity can be studied in nanotube quantum dots.

In quantum dots made out of singlewalled carbon nanotubes (SWNTs), contacts play a crucial role in their transport properties: in the highly transparent regime, Fabry-Pérot (FP) interference patterns in the differential conductance can be observed, whereas in the less transparent case, Coulomb-blockade peaks occur. In the intermediate regime, zero-bias conductance peaks alternate with Coulomb-blockaded valleys, highlighting Kondo resonances below Kondo temperature $T_K$ due to odd numbers of spin in the cotunneling process between the dot and the leads.

Gate-controlled proximity-induced supercurrent has been reported both in SWNTs7–12 and in MWNTs. Reasonable agreement with resonant quantum dot weak link theories18 has been reached in best of the samples (see, e.g., Ref. 9). In some of the experiments, Kondo-restored supercurrents were found in the otherwise Coulomb-blockaded Josephson-junction case. In addition, when $T_K < \Delta$, Josephson junctions have been observed.

Here we report a study of gate-tunable proximity-induced supercurrents of an individual SWNT. We compare supercurrents in Fabry-Pérot and Kondo regimes at the same normal-state conductance and find smaller critical currents in the Kondo regime up to $T_K \sim 10\Delta$. In addition, we find that not just $T_K$ but also the shape of the Kondo resonance conductance peak affects the magnitude of the supercurrent: resonances with zero-field splitting, which appear in about every second of our Kondo peaks, result in a smaller critical current than for the regular Kondo maxima.

Our nanotube samples were made using surface chemical-vapor deposition (CVD) growth with Fe catalyst directly on oxidized heavily doped SiO$_2$/Si wafer. The electrically conducting substrate works as a back gate, separated from the sample by 150 nm of SiO$_2$. A sample with $L=0.7\mu m$ length and $\phi=2$ nm diameter was located using an atomic force microscope and the contacts on the SWNT were made using standard e-beam overlay lithography. For the contacts, 10 nm of Ti was first evaporated, followed by 70 nm of Al, in order to facilitate proximity-induced superconductivity in Ti. Last, 5 nm of Ti was deposited to prevent the Al layer from oxidation. The width of the two contacts was 200 nm and the separation between the them was 0.3 $\mu$m.

The measurement leads were filtered using an RC filter with time constant of 10 $\mu$s at 1 K, followed by twisted pairs with tight, grounded electrical shields for filtering between the still and the mixing chamber, while the final section was provided by a 0.7-m-long Thermocouple cable on the sample holder. In the measurements, differential conductance $G_{d}=dI/dV$ was recorded using standard lock-in techniques. Voltage bias was imposed via a room-temperature voltage divider. The normal-state data were obtained by applying a magnetic field of $B \sim 70$ mT perpendicular to the nanotube. The superconducting gap of the device was taken from the $2\Delta$ quasiparticle peak in voltage-biasing transport measurement, which gives $\Delta=125$ $\mu$eV, and gate capacitance $C_g=1.6$ aF was estimated from the measured gate period of 0.1 V.

The data presented in this Brief Report have been measured in several cool downs, thermal cycles, that have changed the contact conditions on our sample. In the first cool down, the sample showed a strongly asymmetric Fabry-Pérot pattern with one low-transmission (spin-degenerate) channel and another one with high transmission; the zero-bias conductance was limited to $2e^2/h$ as a consequence. A scan of differential conductance $G_{d}(V_{ds},V_{g})$ versus bias voltage $V_{ds}$ and gate voltage $V_g$ is shown in Fig. 1(a) at $B \sim 70$ mT. In the absence of magnetic field, a gate-voltage-dependent supercurrent is observed in the SWNT. The measured critical supercurrent $I_{CM}$ varies periodically with the gate voltage $V_g$, reaching a maximum of 4.8 nA at zero-bias normal-state conductance $G_{N}=G_{d}|_{V_{ds}=V_{g}=0}=2.03e^2/h$. The $I_{CM}R_N$ product is $V_g$ dependent and it changes in a similar fashion as $I_{CM}$ and the inverse of the normal-state resistance $G_{N}$. This result is similar to what has been observed in a
The normal-state differential conductance $G_d$ on the plane spanned by bias voltage $V_{ds}$ and gate voltage $V_g$ in (a) Fabry-Pérot regime and (b) Kondo regime both at $T=30$ mK. Normal states were achieved in all the cases with a magnetic field $B = 70$ mT. Red (light gray) and blue (dark gray) arrows in (b) refer to two types of resonance peaks, which have one magnitude difference in $I_{CM}$ with similar Kondo temperature $T_K$. See text for more details.

FIG. 1. (Color online) Normal-state differential conductance $G_d$ on the plane spanned by bias voltage $V_{ds}$ and gate voltage $V_g$ in (a) Fabry-Pérot regime and (b) Kondo regime both at $T=30$ mK. Normal states were achieved in all the cases with a magnetic field $B = 70$ mT. Red (light gray) and blue (dark gray) arrows in (b) refer to two types of resonance peaks, which have one magnitude difference in $I_{CM}$ with similar Kondo temperature $T_K$. See text for more details.

After a few thermal cycles, the transport of SWNT in Fabry-Pérot regime.

The superconducting $I-V$ curves at a few gate voltage values in (a) Fabry-Pérot regime and (b) Kondo regime. The circles on each $I-V$ curve show how the measured critical current $I_{CM}$ was determined (Ref. 22). $I_{CM}$ versus zero-bias normal-state conductance $G_N$, measured for a resonance with $T_K=14$ K, is displayed in (c) where the black dots and red (light gray) triangles refer to Fabry-Pérot (several resonances) and Kondo data, respectively. Data in (a) were measured in the same cool down as Fig. 1(a) at $T=60$ mK; data in (b) were taken from another cool down after Fig. 1(b) at $T=60$ mK with uncharged $G_N$. The current of the smallest $I_{CM}$ curve in (b) has been amplified by a factor of 5 for clarity. Black and red (light gray) solid lines in (c) are theoretical fits using Eq. (1).

FIG. 2. (Color online) Superconducting $I-V$ curves at a few gate voltage values in (a) Fabry-Pérot regime and (b) Kondo regime. The circles on each $I-V$ curve show how the measured critical current $I_{CM}$ was determined (Ref. 22). $I_{CM}$ versus zero-bias normal-state conductance $G_N$, measured for a resonance with $T_K=14$ K, is displayed in (c) where the black dots and red (light gray) triangles refer to Fabry-Pérot (several resonances) and Kondo data, respectively. Data in (a) were measured in the same cool down as Fig. 1(a) at $T=60$ mK; data in (b) were taken from another cool down after Fig. 1(b) at $T=60$ mK with uncharged $G_N$. The current of the smallest $I_{CM}$ curve in (b) has been amplified by a factor of 5 for clarity. Black and red (light gray) solid lines in (c) are theoretical fits using Eq. (1).
As in the FP regime, the largest critical current over a Kondo resonance corresponds to the peak of the normal-state conductance. In addition, the magnitude of $I_{CM}$ depends on the width of the resonance in bias voltage, i.e., $I_{CM}$ on $T_K$. We have fitted the conductance peaks $G_d(V_d)$ with a Lorentzian function in order to extract the Kondo temperature $T_K$. The resulting $I_{CM}-T_K$ correlation is plotted in Fig. 3 which displays two branches, instead of a single-valued correlation as observed by Grove-Rasmussen et al.16 The upper and lower branches involve the resonance peaks marked in Fig. 1 by red and blue arrows, respectively. Due to the problem of trapped charge fluctuating on the back gate, we have been forced to present only data on which we are sure of the identification between critical current and normal-state conductance. As shown in the inset of Fig. 3, in the data of the lower branch, there is a small dip on the zero-bias conductance peak signifying zero-field splitting of the Kondo resonances marked by blue arrows. The Lorentzian fitting on the split peaks is somewhat approximative, and the fitted $T_K$ remains a bit smaller than from the true half width. Nevertheless, this uncertainty is insignificant on the scale of separation of the upper and lower branches in Fig. 3. Notice that $k_BT_K < E_C > \Delta \propto k_BT$ is valid for all of the measured resonance peaks, which indicates that the transport mechanism is dominated by Kondo effect and Coulomb blockade.

Zero-field splitting seems to take place in our data in every second Kondo resonance, as seen in the nearly alternating sequence of red and blue arrows in Fig. 1(b). Previously zero-field Kondo-peak splitting has been reported in Ref. 23, where the splitting originates from magnetic impurity, which is different from our case as the splitting should then be seen at all the Kondo resonances. Using the standard fourfold shell-filling sequence, it is hard to explain our findings. Split Kondo ridges may be observable when the dot is occupied by two electrons ($N=2$),3,24 and the energy scale of the splitting equals to the gap between singlet ground state and triplet excited state. This, however, should be bordered from both sides by standard spin-half Kondo peaks, a sequence that we cannot identify in our data. From the normal-state bias maps, the characteristic zero-field splitting energy can be estimated as $\Delta_{2BS} \sim 4$ meV, which is well above MAR peak of superconducting electrodes $2\Delta = 0.25$ meV and the typical singlet-triplet excitation energy as found in Ref. 3. We conjecture that the observed zero-field splitting is related to the SU(4) Kondo effect which is peculiar to carbon nanotubes25,26 and which has been shown to lead to a dip in the density of states at small energies,27 which can also suppress the superconducting critical current. Alternatively, zero-field splitting may be related with the recent observation of non-negligible spin-orbit coupling in SWNTs28 which can result in the large splitting energy we observed. In any case, SU(4) Kondo can explain the unusually high $T_K$ by the enhanced degeneracy of a multiple-level quantum dot.29

According to theory,30 the width of Andreev levels can be substantially renormalized by the Kondo effect, which would also modify the IV curve. In order to look for the gap renormalization, we have extracted the excess current $I_{ex}$ as a function of normal-state transmission coefficient $\alpha$, which is displayed in Fig. 4, with $\alpha$ calculated from $\alpha = G_d/(2e^2/h)$, and $I_{ex}$ determined by the difference of integration from $G_dV_d$ curves in superconducting/normal state like in Ref. 31. The relation between $I_{ex}$ and $\alpha$ in a quantum point contact32–34 can be written as $I_{ex} = I_{ex1} + I_{ex2}$, where

$$I_{ex1} = \frac{e\Delta}{h} \left( \frac{2}{2-\alpha} \right)^{\alpha^2} \ln \left[ \frac{1 + \left( 2 \left( 1 - \alpha/(2-\alpha) \right)^{1/2} \right)}{1 - \left( 2 \left( 1 - \alpha/(2-\alpha) \right)^{1/2} \right)} \right].$$

$$I_{ex2} = \frac{e\Delta}{h} \left( \frac{2 - \alpha}{2(1-\alpha)^{3/2}} \ln \left( \frac{1 - \sqrt{1-\alpha}}{1 + \sqrt{1-\alpha}} \right) \right).$$

The blue curve in Fig. 4(a) illustrates Eq. (2) with $\Delta = 100 \mu$eV, indicating a gap renormalization of $\Delta/\Delta = 0.8$. We have also investigated the relation between $I_{ex}$ and $I_{CM}$ at
which yield a linear relation with $\alpha^{2}$. MAR-induced current at large bias voltage gives $I_{\text{AR}} = 4e\Delta/h$. By taking into account that $I_{0} \sim L_{b}/d_{0}$, we get $I_{\text{AR}}/I_{\text{CM}} \sim L_{b}/d_{0}$, which is close to the measured $I_{\text{ex}}/I_{\text{CM}}$ value.

In summary, we have investigated experimentally the proximity-effect-induced supercurrents in SWNTs in the Kondo regime and compared them with results in the Fabry-Pérot regime with equivalent conductance. In the Kondo regime, two different types of resonances, either split or non-split at zero-bias, were observed and this behavior reflects also in the magnitude of supercurrent that displayed two branches vs $T_{K}$. The excess current in Kondo regime was analyzed using MAR theory and renormalization of Andreev levels by 80% was obtained.

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20. This value does not include the effect of finite length of the nanotube, which would suppress the maximum $I_{0}$ a bit. See, e.g., A. V. Galaktionov and A. D. Zaikin, Phys. Rev. B 65, 184507 (2002).


22. When NDR exists, we extract $I_{\text{CM}}$ from the local current maximum $I_{\text{CM}}$ and minimum $I_{\text{CM}}$ using $I_{\text{CM}}=\left(I_{\text{CM}}^{+}+I_{\text{CM}}^{-}\right)/2$. Around the Kondo resonance peaks without NDR, $I_{\text{CM}}$ is obtained using the averaged voltages, $V_{\text{CM}}^{+}$ and $V_{\text{CM}}^{-}$, respectively, of $I_{\text{CM}}^{+}$ and $I_{\text{CM}}^{-}$ peak positions at lower $I_{\text{CM}}$ and taking $I_{\text{CM}}=R_{\text{CM}}^{+}V_{\text{CM}}^{-}+R_{\text{CM}}^{-}V_{\text{CM}}^{+}$.


